# 2SD2375

## Silicon NPN triple diffusion planar type

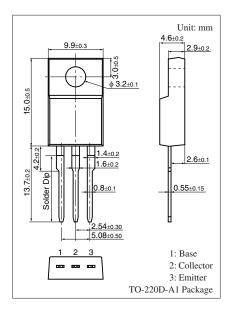
For power amplification with high forward current transfer ratio

### ■ Features

- High forward current transfer ratio h<sub>FE</sub> which has satisfactory linearity
- Full-pack package which can be installed to the heat sink with one screw

## ■ Absolute Maximum Ratings $T_C = 25$ °C

Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)	V <sub>CBO</sub>	80	V	
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	60	V	
Emitter-base voltage (Collector open)	$V_{EBO}$	6	V	
Collector current	$I_{C}$	3	A	
Peak collector current	$I_{CP}$	6	A	
Base current	$I_{B}$	1	A	
Collector power dissipation	P <sub>C</sub>	25	W	
$T_a = 25$ °C		2.0		
Junction temperature	$T_{j}$	150	°C	
Storage temperature	$T_{stg}$	-55 to +150	°C	



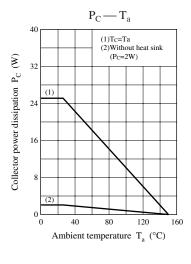
### ■ Electrical Characteristics $T_C = 25$ °C $\pm 3$ °C

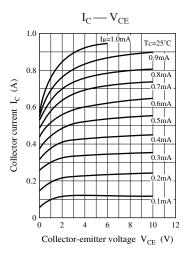
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	$I_C = 25 \text{ mA}, I_B = 0$	60			V
Collector-base cutoff current (Emitter open)	$I_{CBO}$	$V_{CB} = 80 \text{ V}, I_E = 0$			100	μΑ
Collector-emitter cutoff current (Base open)	I <sub>CEO</sub>	$V_{CE} = 40 \text{ V}, I_{B} = 0$			100	μΑ
Emitter-base cutoff current (Collector open)	$I_{EBO}$	$V_{EB} = 6 \text{ V}, I_C = 0$			100	μΑ
Forward current transfer ratio *	$h_{FE}$	$V_{CE} = 4 \text{ V}, I_{C} = 0.5 \text{ A}$	500		1 500	_
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	$I_C = 2 A, I_B = 0.05 A$			1.0	V
Transition frequency	$f_T$	$V_{CE} = 12 \text{ V}, I_{C} = 0.2 \text{ A}, f = 10 \text{ MHz}$		50		MHz

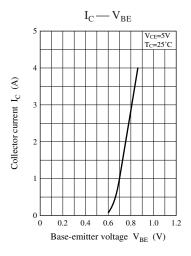
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

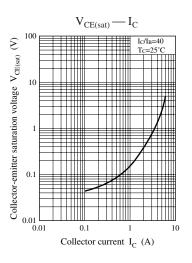
### 2. \*: Rank classification

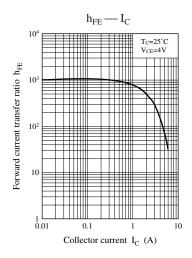
Rank	Q	Р
$h_{FE}$	500 to 1000	800 to 1 500

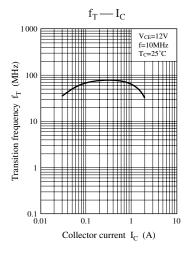


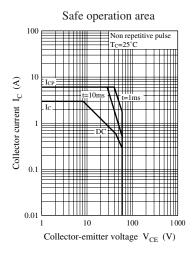


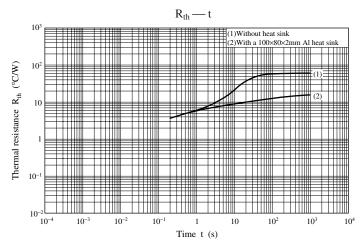












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